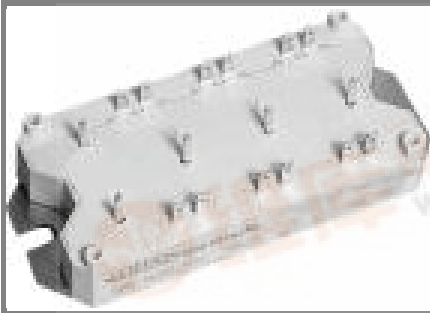


# SKM 100GD063DL



**SEMITRANS™ 6**

## Superfast NPT-IGBT Module

SKM 100GD063DL

### Features

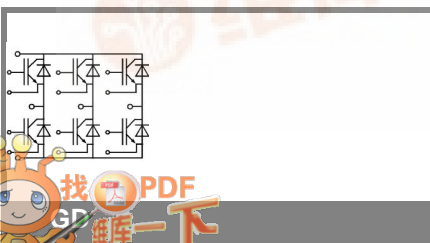
- Homogeneous Si
- Si structure (NPT IGBT)
- $V_{CE(sat)}$  with positive temperature coefficient
- High short circuit capability, self limiting to  $6 \times I_C$

### Typical Applications

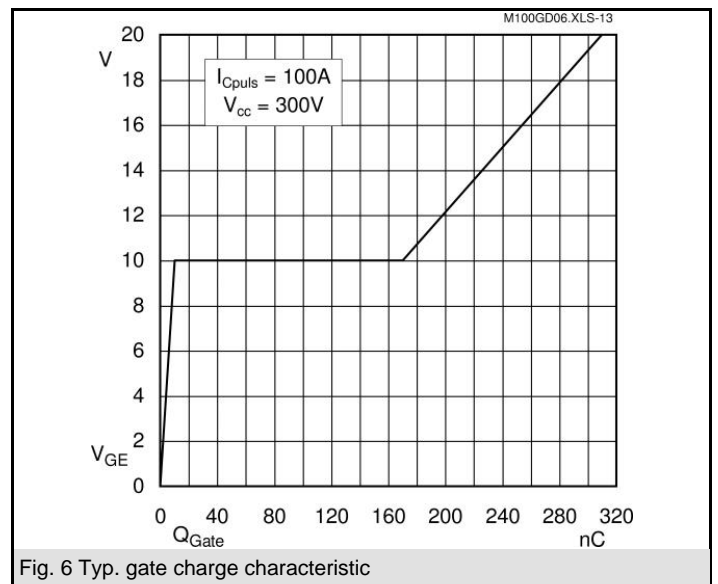
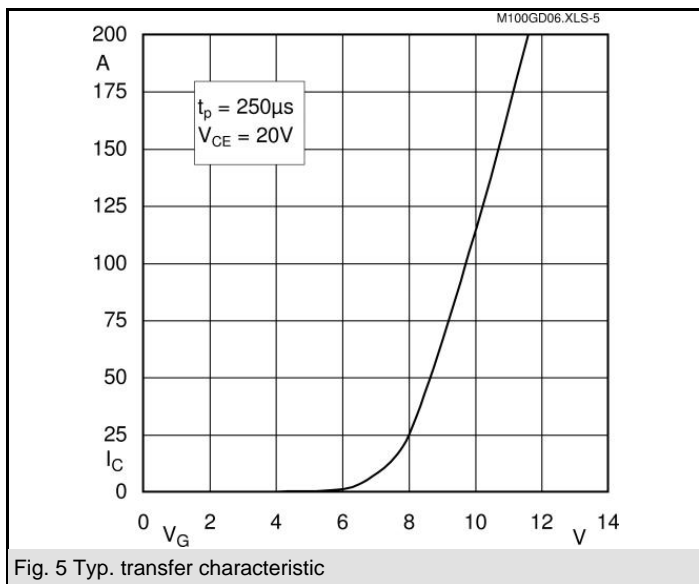
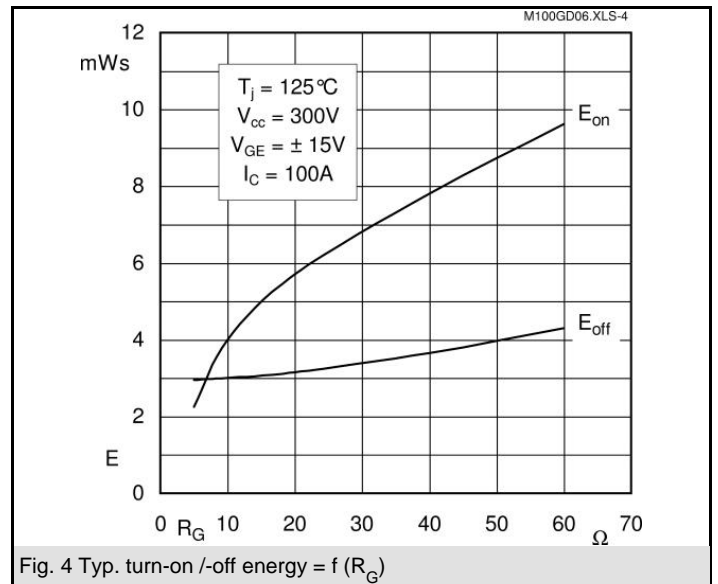
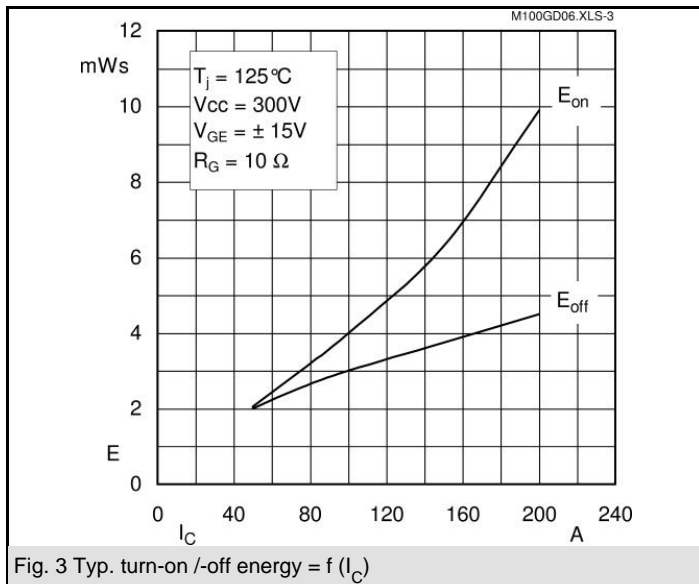
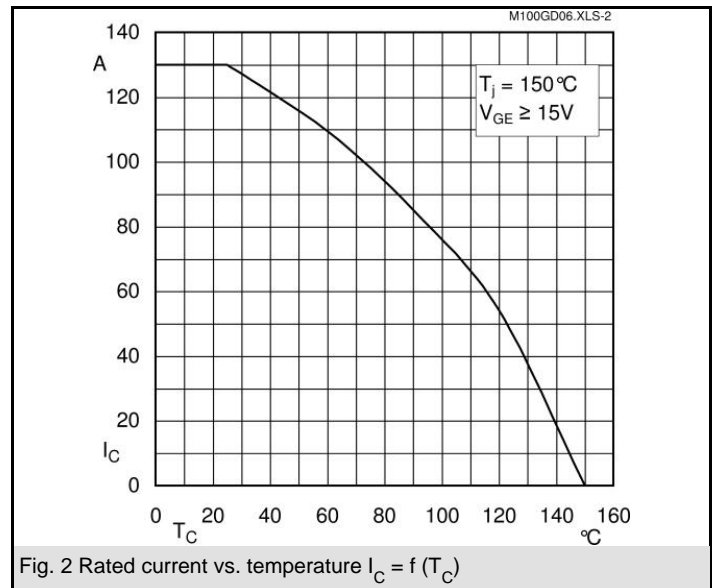
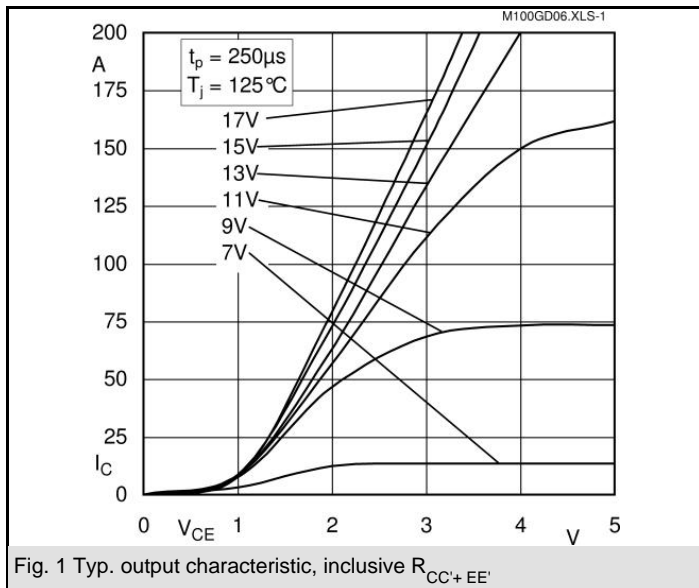
- Switched mode power supplies
- Three phase inverters for AC motor speed control
- For  $f_{sw} > 10$  kHz

Absolute Maximum Ratings		$T_{case} = 25^\circ\text{C}$ , unless otherwise specified		
Symbol	Conditions	Values		Units
<b>IGBT</b>				
$V_{CES}$		600		V
$I_C$	$T_c = 25$ (80) °C	130 (95)		A
$I_{CRM}$	$t_p = 1$ ms	200		A
$V_{GES}$		$\pm 20$		V
$T_{vj}$ , ( $T_{stg}$ )	$T_{OPERATION} \leq T_{stg}$	- 40 ... +150 (125)		°C
$V_{isol}$	AC, 1 min.	2500		V
<b>Inverse diode</b>				
$I_F$	$T_c = 25$ (80) °C	100 (75)		A
$I_{FRM}$	$t_p = 1$ ms	200		A
$I_{FSM}$	$t_p = 10$ ms; sin.; $T_j = 150$ °C	720		A

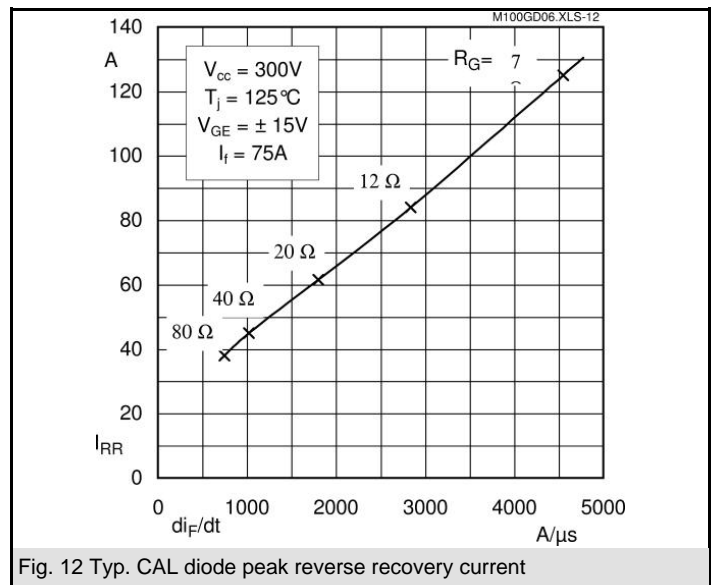
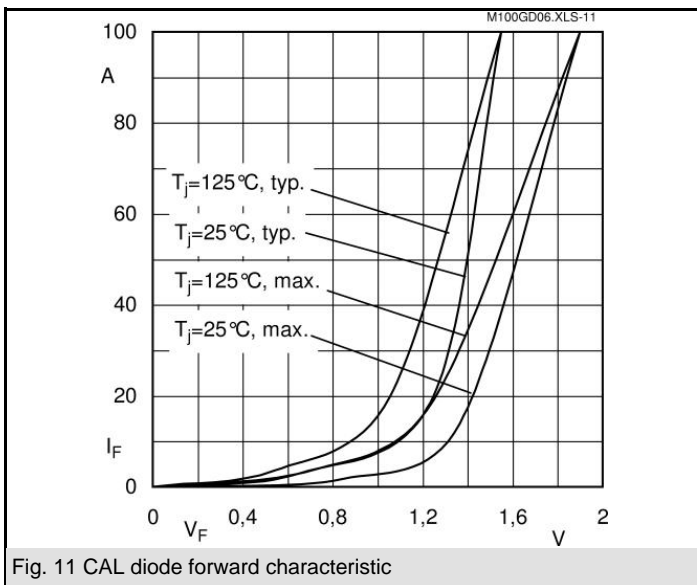
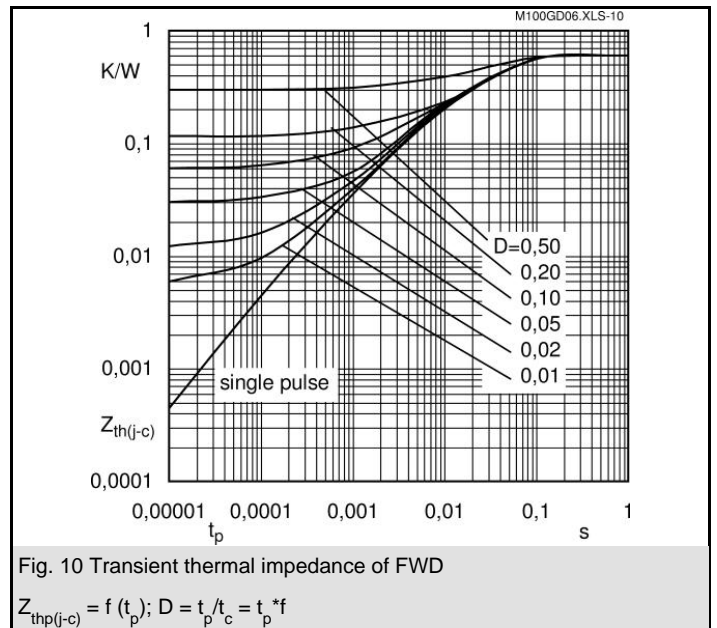
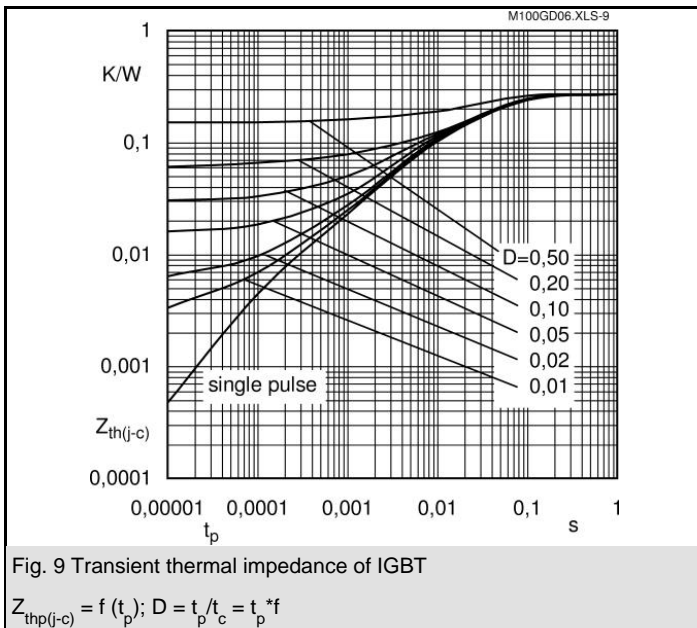
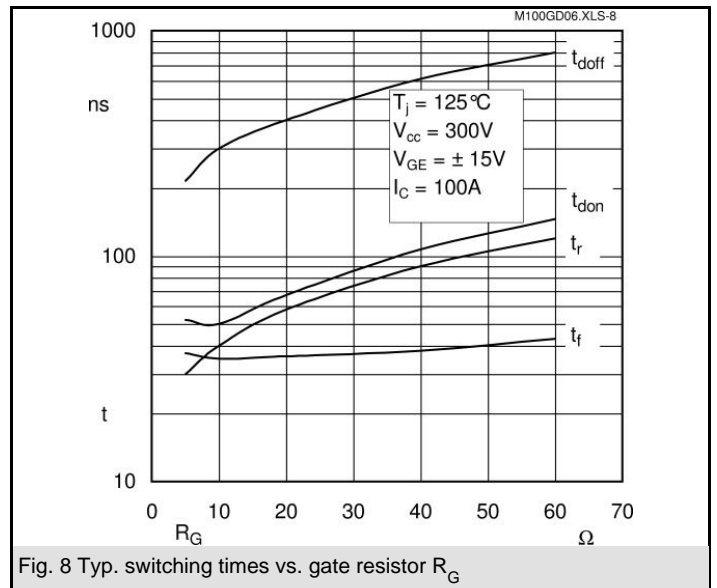
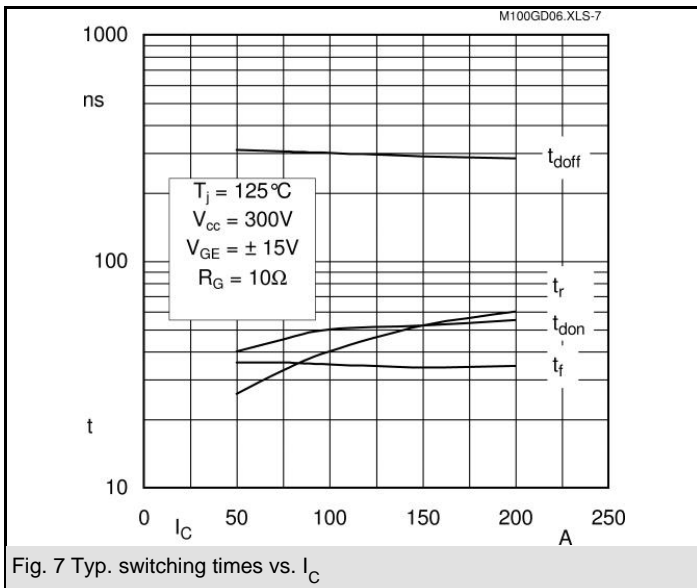
Characteristics		$T_{case} = 25^\circ\text{C}$ , unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
<b>IGBT</b>					
$V_{GE(th)}$	$V_{GE} = V_{CE}$ , $I_C = 3$ mA	4,5	5,5	6,5	V
$I_{CES}$	$V_{GE} = 0$ , $V_{CE} = V_{CES}$ , $T_j = 25$ (125) °C		0,15	0,45	mA
$V_{CE(TO)}$	$T_j = 25$ (125) °C		1,05 (1)		V
$r_{CE}$	$V_{GE} = 15$ V, $T_j = 25$ (125) °C		10,5 (14)		mΩ
$V_{CE(sat)}$	$I_{Cnom} = 100$ A, $V_{GE} = 15$ V, chip level		2,1 (2,4)	2,5 (2,8)	V
$C_{ies}$	under following conditions		5,6		nF
$C_{oes}$	$V_{GE} = 0$ , $V_{CE} = 25$ V, $f = 1$ MHz		0,6		nF
$C_{res}$			0,4		nF
$L_{CE}$				60	nH
$R_{CC+EE}$	res., terminal-chip $T_c = 25$ (125) °C				mΩ
$t_{d(on)}$	$V_{CC} = 300$ V, $I_{Cnom} = 100$ A		50		ns
$t_r$	$R_{Gon} = R_{Goff} = 10$ Ω, $T_j = 125$ °C		40		ns
$t_{d(off)}$	$V_{GE} \pm 15$ V		300		ns
$t_f$			35		ns
$E_{on}$ ( $E_{off}$ )			4 (3)		mJ
<b>Inverse diode</b>					
$V_F = V_{EC}$	$I_{Fnom} = 100$ A; $V_{GE} = 0$ V; $T_j = 25$ (125) °C		1,55 (1,55)	1,9	V
$V_{(TO)}$	$T_j = 25$ (125) °C			0,9	V
$r_T$	$T_j = 25$ (125) °C			10	mΩ
$I_{RRM}$	$I_{Fnom} = 100$ A; $T_j = 125$ ( ) °C		8		A
$Q_{rr}$	$di/dt = 1000$ A/μs		44		μC
$E_{rr}$	$V_{GE} = 0$ V		1,5		mJ
<b>Thermal characteristics</b>					
$R_{th(j-c)}$	per IGBT			0,27	K/W
$R_{th(j-c)D}$	per Inverse Diode			0,6	K/W
$R_{th(c-s)}$	per module			0,05	K/W
<b>Mechanical data</b>					
$M_s$	to heatsink M5	4		5	Nm
$M_t$	to terminals				Nm
w				175	g



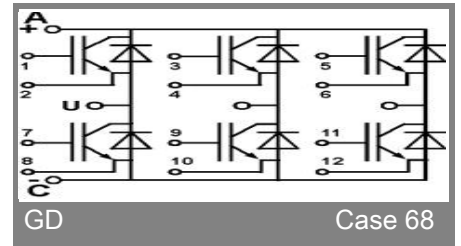
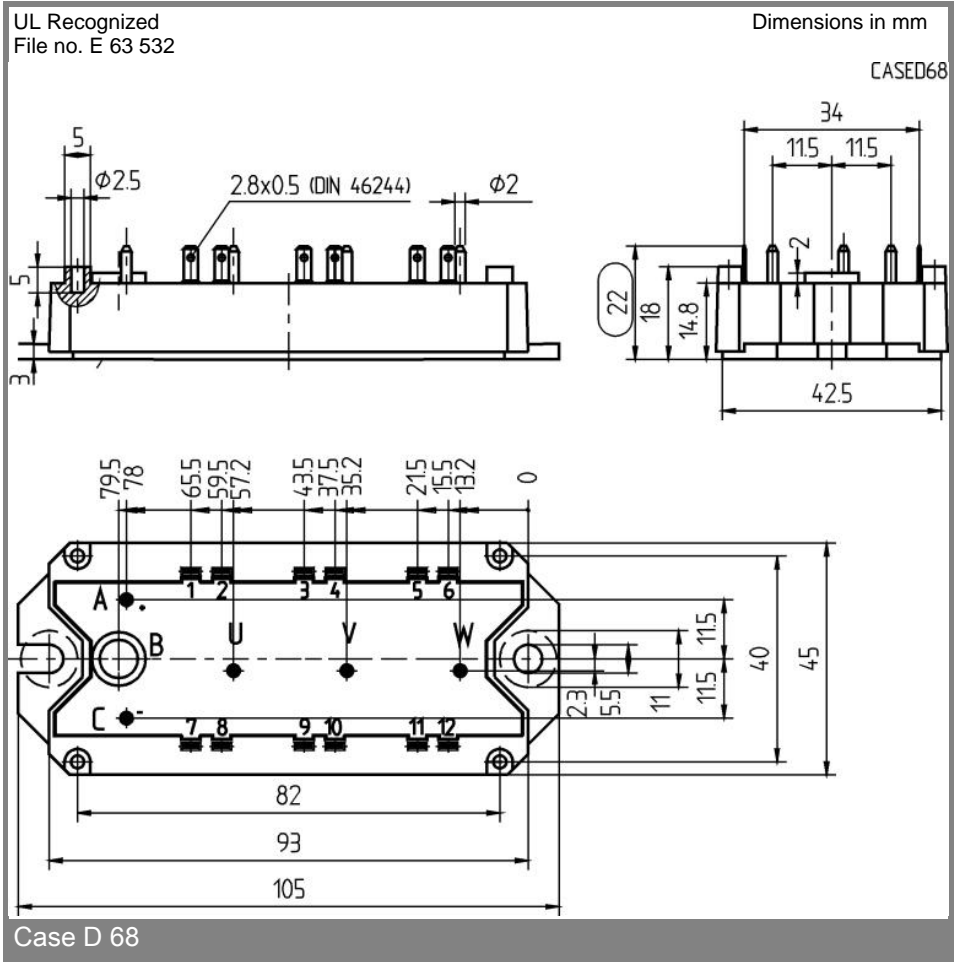
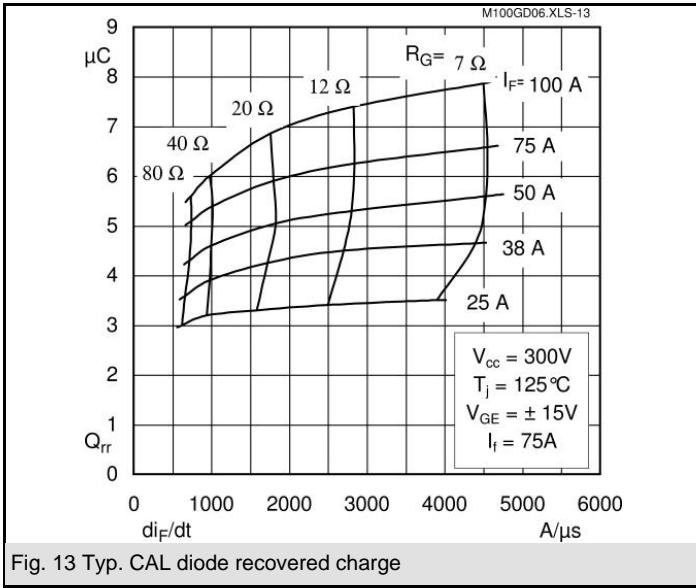
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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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